

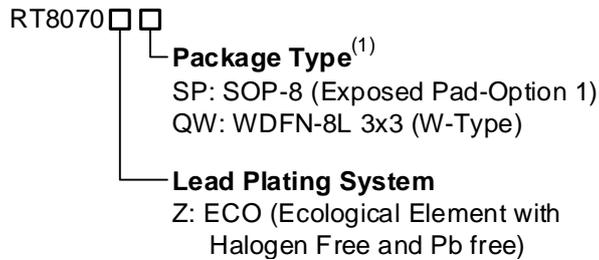
4A, 2MHz, Synchronous Step-Down Converter

1 General Description

The RT8070 is a simple, easy-to-use current mode controlled, 4A synchronous step-down converter with an input supply voltage range from 2.7V to 5.5V. The device features a built-in accurate 0.8V reference voltage and integrates low R_{DS(ON)} power MOSFETs to achieve high efficiency in both WDFN-8L 3x3 and SOP-8 (Exposed Pad) packages. The RT8070 operates in automatic PSM mode, maintaining high efficiency during light load operation. The device includes cycle-by-cycle current-limit protection to prevent catastrophic damage due to output short circuit, overcurrent, or inductor saturation. The adjustable soft-start function prevents inrush current during start-up. The device also features input undervoltage-lockout, output undervoltage protection, and over-temperature protection to ensure safe and smooth operation under all conditions.

The recommended junction temperature range is -40°C to 125°C, and the ambient temperature range is -40°C to 85°C.

2 Ordering Information



Note 1.

Richtek products are Richtek Green Policy compliant and marked with ⁽¹⁾ indicates compatible with the current requirements of IPC/JEDEC J-STD-020.

3 Features

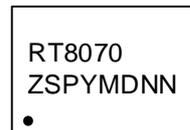
- Input Voltage Range from 2.7V to 5.5V
- Integrated 110mΩ and 70mΩ MOSFETs
- 100% Duty Cycle for Lowest Dropout
- Power Saving Mode for Light Loads
- Adjustable Frequency: 200kHz to 2MHz
- 0.8V Reference Allows Low Output Voltage
- Enable Function
- External Soft-Start
- Power-Good Function
- Input Undervoltage-Lockout Protection
- Output Undervoltage Protection
- Over-Temperature Protection

4 Applications

- LCD TVs and Monitors
- Notebook Computers
- Distributed Power Systems
- IP Phones
- Digital Cameras

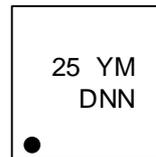
5 Marking Information

RT8070ZSP



RT8070ZSP: Product Code
YMDNN: Date Code

RT8070ZQW



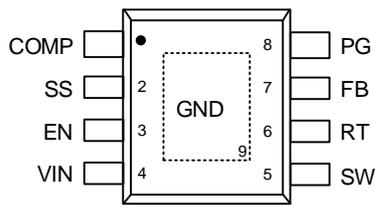
25: Product Code
YMDNN: Date Code

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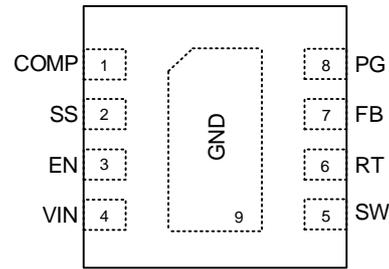
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6 Pin Configuration

(TOP VIEW)



SOP-8 (Exposed Pad)

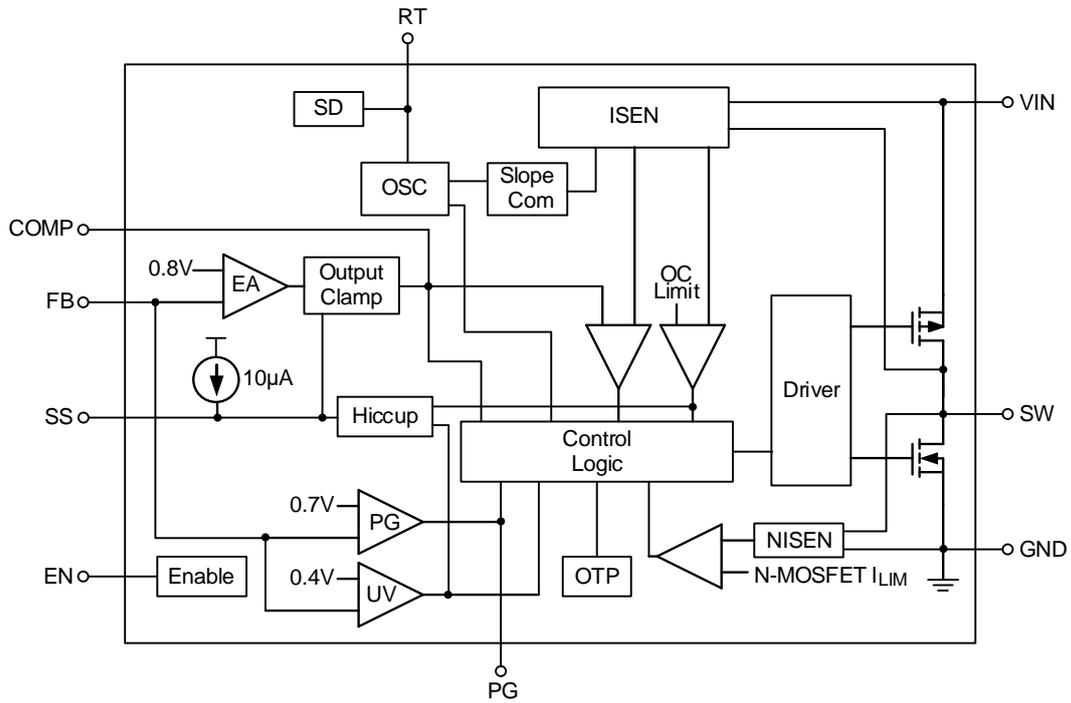


WDFN-8L 3x3

7 Functional Pin Description

Pin No.		Pin Name	Pin Function
SOP-8 (Exposed Pad)	WDFN-8L 3x3		
1	1	COMP	Compensation node. Connect external compensation elements to this pin to stabilize the control loop.
2	2	SS	Soft-start capacitor connection node. Connect an external capacitor between this pin and ground to set the soft-start time.
3	3	EN	Enable control input. Connect this pin to a logic-high to enable the device and connect it to ground to disable the device.
4	4	VIN	Power input. Connect input capacitors between this pin and PGND. It is recommended to use a 10 μ F, X5R, 0805 and a 0.1 μ F, X5R capacitors.
5	5	SW	Switch node between the internal switch and the synchronous rectifier. Connect this pin to the inductor.
6	6	RT	Oscillator resistor input. Connect a resistor from this pin to GND to set the switching frequency.
7	7	FB	Feedback voltage input. Connect this pin to the midpoint of the external feedback resistive divider to set the output voltage of the converter to the desired regulation level. The device regulates the FB voltage at a feedback reference voltage, typically 0.8V.
8	8	PG	Power-good indicator. This pin is an open-drain logic output that is pulled to ground when the output voltage is not within $\pm 12.5\%$ of the regulation point.
9 (Exposed Pad)	9 (Exposed Pad)	GND	GND exposed pad. The exposed pad is internally connected with GND and must be soldered to a large GND plane. Connect this GND plane to other layers with thermal vias to help dissipate heat from the device.

8 Functional Block Diagram



9 Absolute Maximum Ratings

(Note 2)

- Supply Input Voltage, V_{IN} ----- -0.3V to 6V
- SW Pin Switch Voltage ----- -0.3V to 6V
 <10ns----- -2.5V to 8.5V
- Other I/O Pin Voltages ----- -0.3V to 6V
- Power Dissipation, P_D @ $T_A = 25^\circ\text{C}$
 SOP-8 (Exposed Pad) ----- 1.333W
 WDFN-8L 3x3 ----- 1.429W
- Package Thermal Resistance (Note 3)
 SOP-8 (Exposed Pad), θ_{JA} ----- 75°C/W
 SOP-8 (Exposed Pad), θ_{JC} ----- 15°C/W
 WDFN-8L 3x3, θ_{JA} ----- 70°C/W
 WDFN-8L 3x3, θ_{JC} ----- 8.2°C/W
- Lead Temperature (Soldering, 10 sec.)----- 260°C
- Junction Temperature ----- 150°C
- Storage Temperature Range ----- -65°C to 150°C
- ESD Susceptibility (Note 4)
 HBM (Human Body Model) ----- 2kV

Note 2. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 3. θ_{JA} is simulated at $T_A = 25^\circ\text{C}$ on a high effective thermal conductivity four-layer test board per JEDEC 51-7. θ_{JC} is measured at the exposed pad of the package.

Note 4. Devices are ESD sensitive. Handling precautions are recommended.

10 Recommended Operating Conditions

(Note 5)

- Supply Input Voltage, V_{IN} ----- 2.7V to 5.5V
- Ambient Temperature Range ----- -40°C to 85°C
- Junction Temperature Range ----- -40°C to 125°C

Note 5. The device is not guaranteed to function outside its operating conditions.

11 Electrical Characteristics

($V_{IN} = 3.3V$, $T_A = 25^\circ C$, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
VIN Supply Input Operating Voltage	V_{IN}		2.7	--	5.5	V
Feedback Reference Voltage	V_{REF}		0.784	0.8	0.816	V
Supply Current (Quiescent)	I_Q	$V_{EN} = 2V$, $V_{FB} = 0.78V$, not switching	--	460	--	μA
Supply Current (Shutdown)	I_{SHDN}	$V_{EN} = 0V$	--	--	10	μA
Error Amplifier Trans-Conductance	g_m		--	400	--	$\mu A/V$
Current Sense Trans-Resistance	R_T		--	0.3	--	Ω
Switching Frequency	f_{SW}	$R_{RT} = 300k$	0.8	1	1.2	MHz
Switching Frequency Range			0.2	--	2	MHz
EN Input Voltage Rising Threshold	V_{EN_R}	Enable high-level input voltage	1.6	--	--	V
EN Input Voltage Falling Threshold	V_{EN_F}	Enable low-level input voltage	--	--	0.4	V
On-Resistance of High-Side MOSFET	R_{DSON_H}	$I_{LX} = 0.5A$	--	110	180	$m\Omega$
On-Resistance of Low-Side MOSFET	R_{DSON_L}	$I_{LX} = 0.5A$	--	70	120	$m\Omega$
Peak Current Limit	I_{LIM}		4.7	5.8	--	A
Undervoltage-Lockout Rising Threshold	V_{UVLO_R}	V_{IN} rising	--	2.4	--	V
Undervoltage-Lockout Falling Threshold	V_{UVLO_F}	V_{IN} falling	--	2.2	--	V
Soft-Start Time	t_{SS}	$C_{SS} = 10nF$	--	800	--	μs
Power-Good High Threshold		V_{FB} rising, PG goes high	--	87.5	--	% V_{OUT}

12 Typical Application Circuit

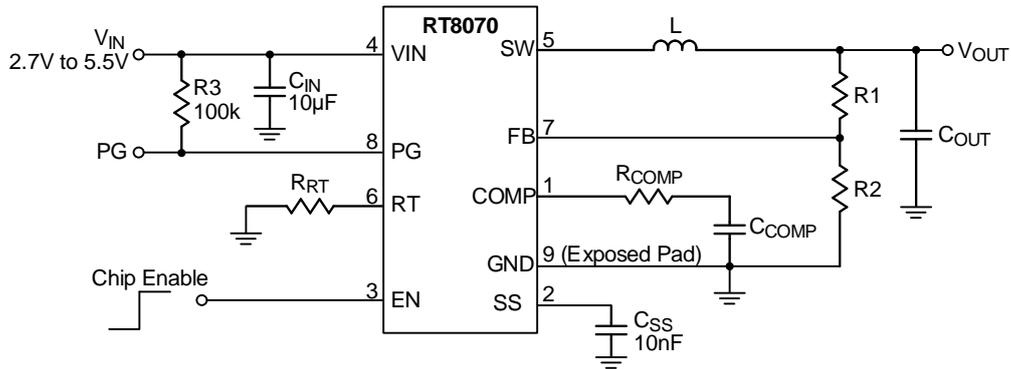


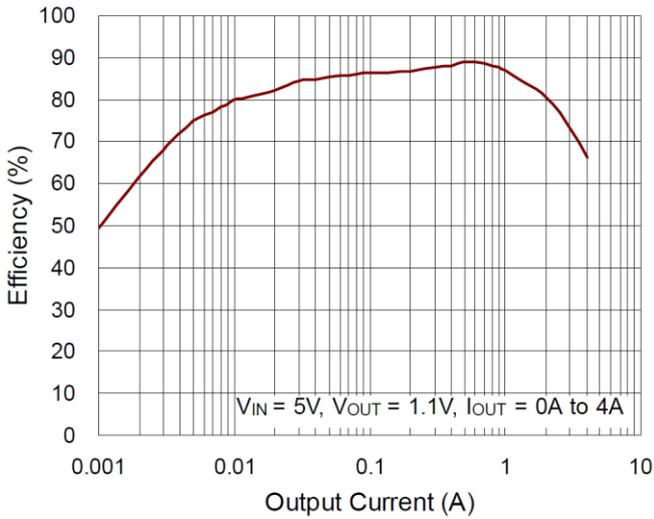
Table 1. Recommended Components Selection for fsw = 1MHz

V _{OUT} (V)	R ₁ (kΩ)	R ₂ (kΩ)	R _{COMP} (kΩ)	C _{COMP} (pF)	L (µH)	C _{OUT} (µF)
3.3	75	24	33	560	2	22
2.5	51	24	22	560	2	22
1.8	30	24	15	560	1.5	22
1.5	21	24	13	560	1.5	22
1.2	12	24	11	560	1.5	22
1	6	24	8.2	560	1.5	22

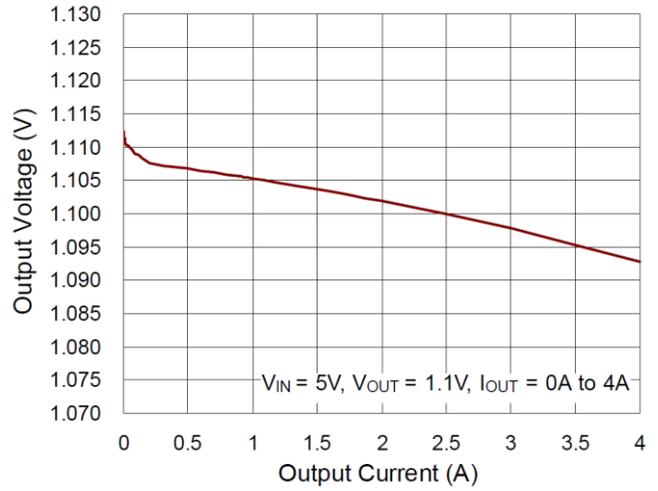
Note 6. Considering the effective capacitance de-rated with biased voltage level and size, the C_{OUT} component needs to satisfy the effective capacitance of at least 15µF at the targeted output level for stable and normal operation.

13 Typical Operating Characteristics

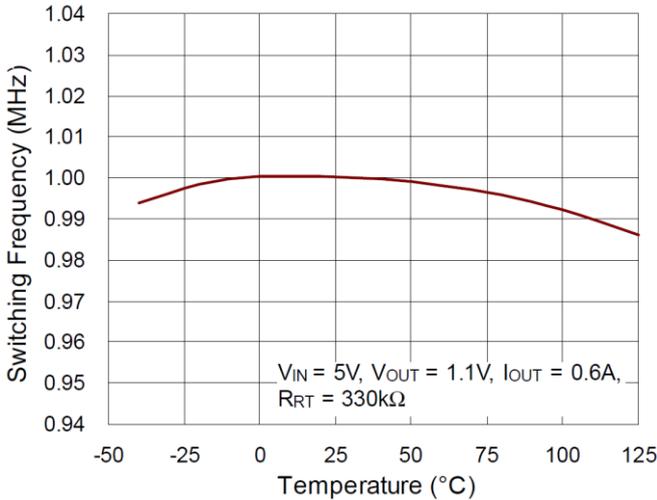
Efficiency vs. Output Current



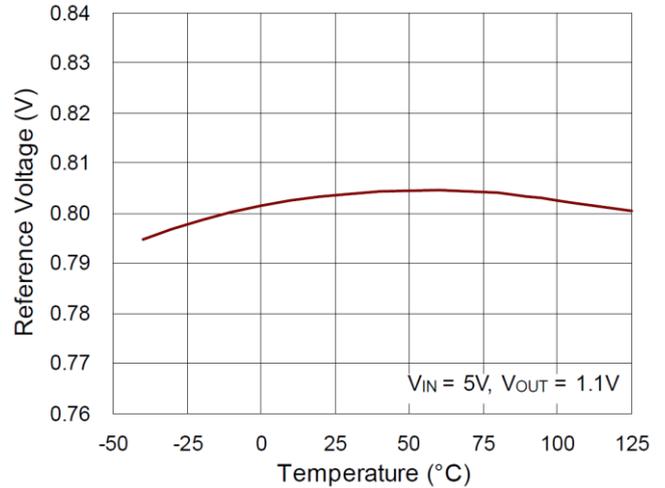
Output Voltage vs. Output Current



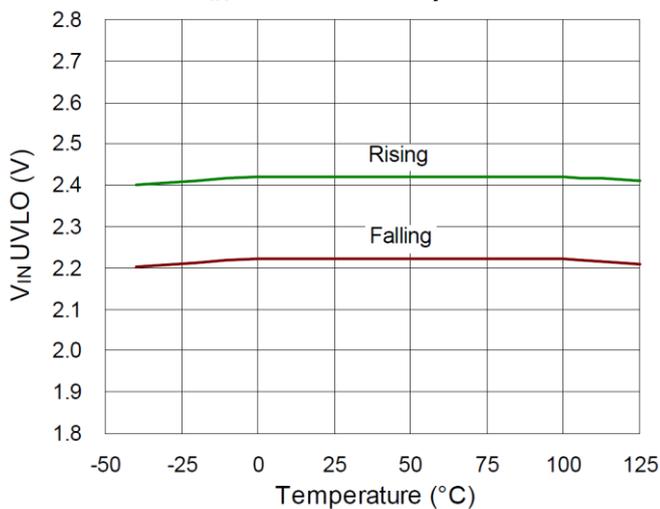
Switching Frequency vs. Temperature



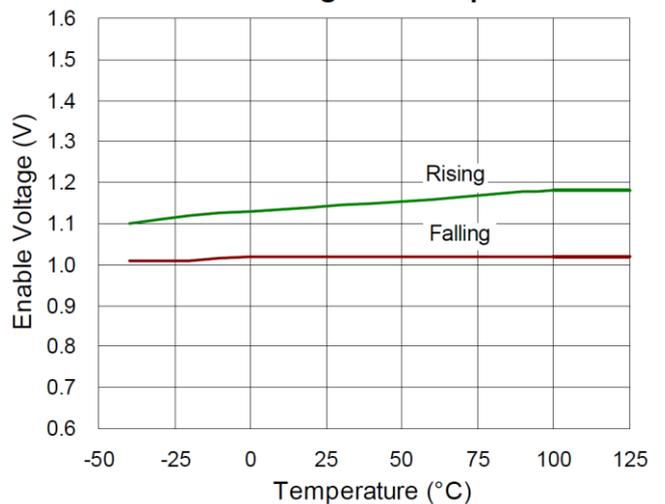
Reference Voltage vs. Temperature



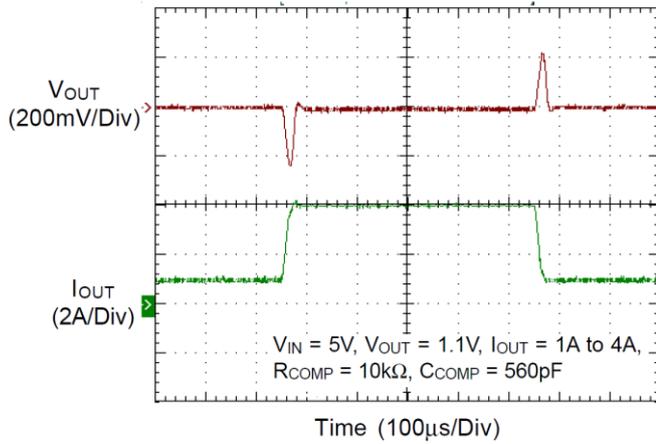
V_{IN} UVLO vs. Temperature



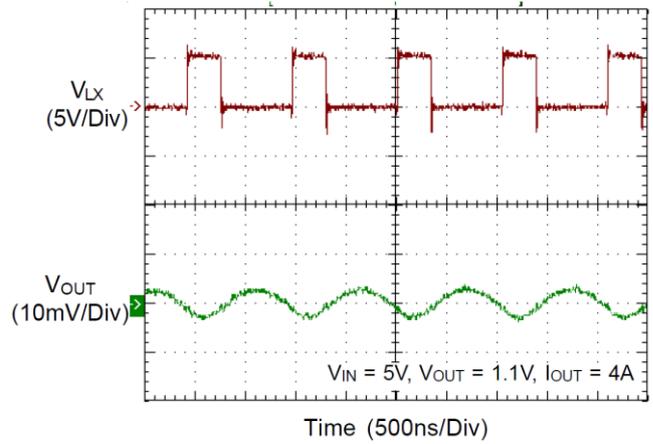
Enable Voltage vs. Temperature



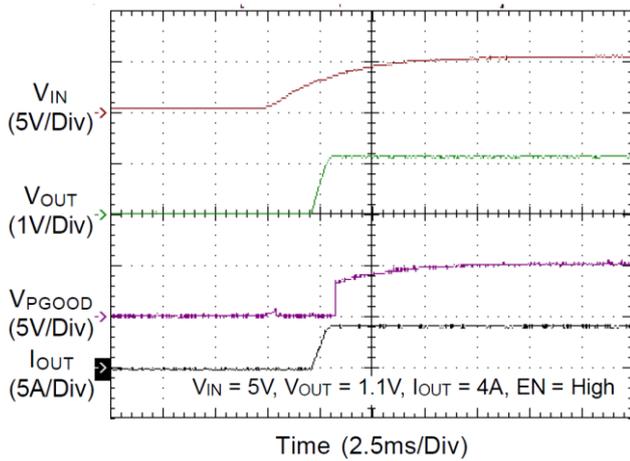
Load Transient Response



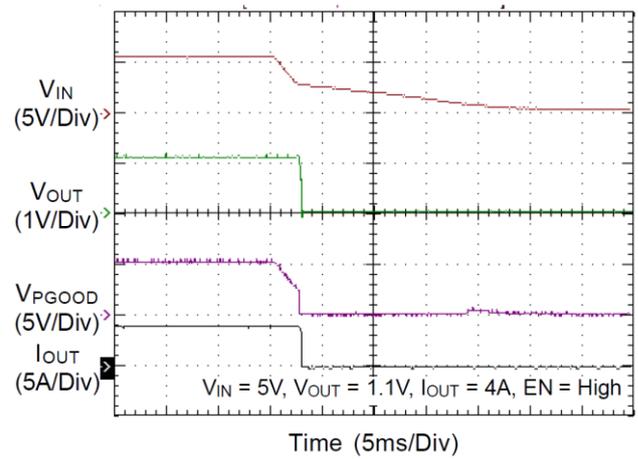
Switching



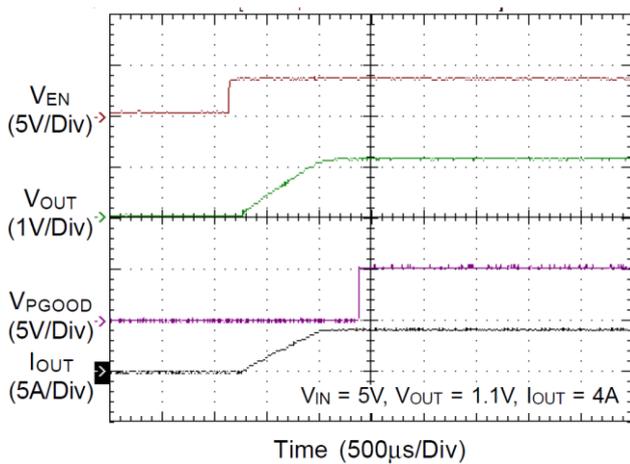
Power On from V_{IN}



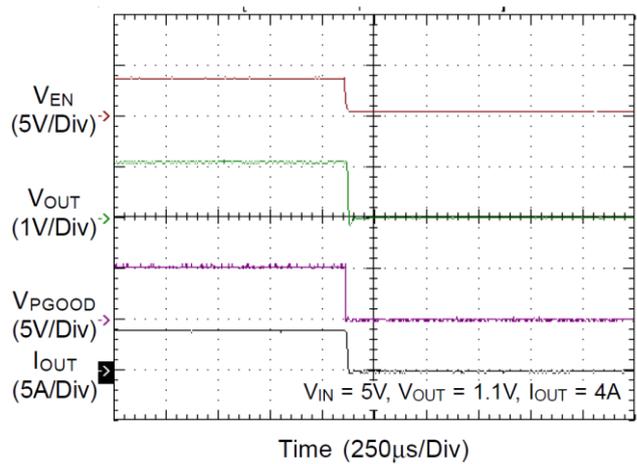
Power Off from V_{IN}



Power On from EN



Power Off from EN



14 Application Information

(Note 7)

The basic IC application circuit is shown in the Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value and operating frequency followed by C_{IN} and C_{OUT}.

14.1 Main Control Loop

During normal operation, the internal high-side power switch (P-MOSFET) is turned on at the beginning of each clock cycle. Current in the inductor increases until the peak inductor current reaches the value defined by the output voltage (V_{COMP}) of the error amplifier. The error amplifier adjusts its output voltage by comparing the feedback signal from a resistive voltage divider on the FB pin with an internal 0.8V reference. When the load current increases, it causes a reduction in the feedback voltage. The error amplifier increases its output voltage until the average inductor current matches the new load current. When the high-side power MOSFET turns off, the low-side power switch (N-MOSFET) turns on until the beginning of the next clock cycle.

14.2 Output Voltage Setting

The output voltage is set by an external resistive voltage-divider according to the following equation:

$$V_{OUT} = V_{REF} \times \left(1 + \frac{R1}{R2}\right)$$

where V_{REF} equals to 0.8V (typical).

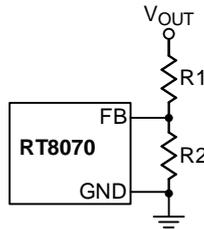


Figure 1. Output Voltage Setting

14.3 Soft-Start Function

The RT8070 provides an adjustable soft-start function. The soft-start function is used to prevent a large inrush current while the converter is being powered up. For the RT8070, the soft-start timing can be programmed by the external capacitor C_{SS} between the SS pin and ground. An internal current source I_{SS} (10μA) charges an external capacitor to build a soft-start ramp voltage. The V_{FB} will track the internal ramp voltage during the soft-start interval. The typical soft-start time is that V_{OUT} rises from zero to 90% of the setting value and can be calculated using the following equation:

$$t_{SS} = C_{SS} \times \frac{0.8}{I_{SS}}$$

14.4 Power-Good Output

The power-good output is an open-drain output and requires a pull-up resistor. When the output voltage is 12.5% above or 12.5% below its set voltage, PG will be pulled low. It is held low until the output voltage returns to within the allowed tolerances. During soft-start, PG is actively held low and is only allowed to transition high when soft-start is completed and the output voltage reaches 87.5% of its set voltage.

14.5 Switching Frequency Setting

The RT8070 offers an adjustable switching frequency setting, which can be configured using an external resistor R_T . The switching frequency range is from 200kHz to 2MHz. The selection of the operating frequency is a trade-off between efficiency and component size. High frequency operation allows the use of smaller inductor and capacitor values. Operation at lower frequencies improves efficiency by reducing internal gate charge and transition losses but requires larger inductance and capacitance values to maintain low output ripple voltage. An additional constraint on operating frequency is the minimum on-time and minimum off-time. The minimum on-time, t_{ON_MIN} , is the smallest duration of time in which the high-side switch can be in its “on” state. This time is typically 90ns. In continuous mode operation, the minimum on-time limit imposes a maximum operating frequency, f_{SW_MAX} , of:

$$f_{SW_MAX} = V_{OUT} / (t_{ON_MIN} \times V_{IN_MAX})$$

where V_{IN_MAX} is the maximum operating input voltage. The switching frequency f_{sw} can be set using an external resistor R_T connected between the R_T pin and ground. The equation below shows the relationship between the switching frequency and the R_T value.

$$f_{sw} \text{ (MHz)} = K \times 0.9 / R_{RT} \text{ (k}\Omega\text{)}$$

where $K = 3.67 \times 10^5$

Note that the variation of f_{sw} is $\pm 15\%$.

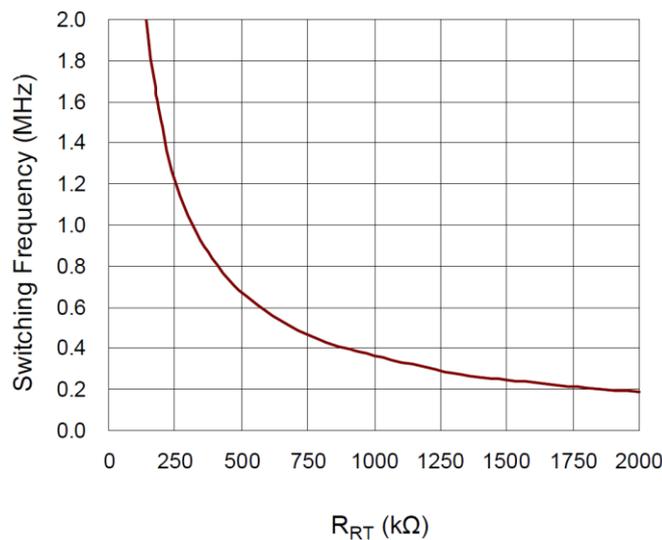


Figure 2. Switching Frequency vs. RRT Resistor

14.6 Inductor Selection

For a given input and output voltage, the inductor value and operating frequency determine the ripple current. The ripple current, ΔI_L , increases with higher V_{IN} and decreases with higher inductance:

$$\Delta I_L = \left[\frac{V_{OUT}}{f \times L} \right] \left[1 - \frac{V_{OUT}}{V_{IN}} \right]$$

Lower ripple current reduces not only the ESR losses in the output capacitors but also the output voltage ripple. The highest efficiency operation is achieved by reducing ripple current at low frequencies, but attaining this goal requires a large inductor.

For the ripple current selection, the value of $\Delta I_L = 0.4 (I_{MAX})$ is a reasonable starting point. The largest ripple current occurs at the highest V_{IN} . To guarantee that the ripple current stays below a specified maximum value, the inductor value should be chosen according to the following equation:

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_{L(MAX)}} \right] \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}} \right]$$

14.7 Using Ceramic Input and Output Capacitors

Higher values, lower-cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating, and low ESR make them ideal for switching regulator applications. However, care must be taken when these capacitors are used at the input and output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input. At best, this ringing can couple to the output and be mistaken for loop instability. At worst, a sudden inrush current through the long wires can potentially cause a voltage spike at V_{IN} large enough to damage the part.

14.8 Slope Compensation and Peak Inductor Current

Slope compensation provides stability in constant frequency architectures by preventing sub-harmonic oscillations at duty cycles greater than 50%. It is accomplished internally by adding a compensating ramp to the inductor current signal. Normally, the peak inductor current is reduced when slope compensation is added. However, for this IC, a separate inductor current signal is used to monitor the overcurrent condition, so the maximum output current stays relatively constant regardless of the duty cycle.

14.9 Hiccup Mode Undervoltage Protection

A hiccup mode undervoltage protection (UVP) function is provided for the IC. When the FB voltage drops below half of the feedback reference voltage, V_{FB} , the UVP function is triggered to automatically re-soft-start the power stage until this event is cleared. The hiccup mode UVP reduces the input current in short circuit conditions but will not be triggered during the soft-start process.

14.10 Undervoltage-Lockout Protection

The RT8070 includes an input undervoltage-lockout protection (UVLO) function. If the input voltage exceeds the UVLO rising threshold voltage, the converter will reset and prepare the PWM for operation. However, if the input voltage falls below the UVLO falling threshold voltage during normal operation, the device will stop switching. The UVLO rising and falling threshold voltages have hysteresis to prevent noise-induced resets.

14.11 Over-Temperature Protection

The RT8070 includes over-temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. The OTP will shut down switching operation when the junction temperature exceeds the over-temperature protection threshold T_{SD} (150°C). Once the junction temperature cools down by the over-temperature protection hysteresis ($\Delta T_{SD} = 20^\circ\text{C}$), the IC will resume normal operation with a complete soft-start.

14.12 Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated

using the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature; T_A is the ambient temperature; and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a SOP-8 (Exposed Pad) package, the thermal resistance, θ_{JA} , is 75°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. For a WDFN-8L 3x3 package, the thermal resistance, θ_{JA} , is 70°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated as below:

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (75^\circ\text{C/W}) = 1.333\text{W for a SOP-8 (Exposed Pad) package.}$$

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (70^\circ\text{C/W}) = 1.429\text{W for a WDFN-8L 3x3 package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curves in [Figure 3](#) allow the designer to see the effect of rising ambient temperature on the maximum power dissipation.

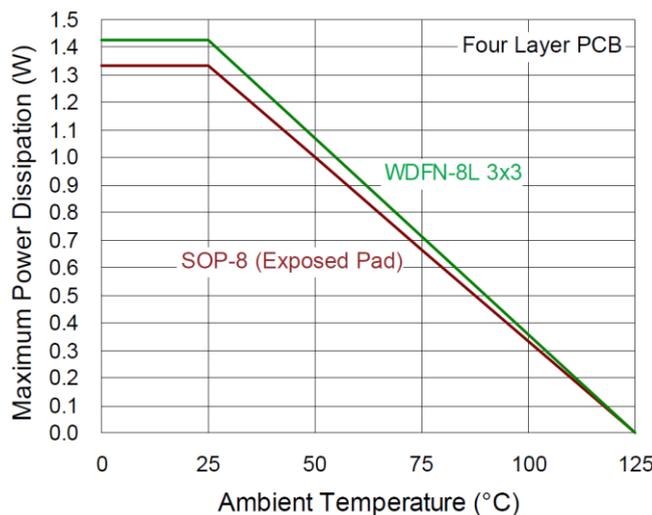
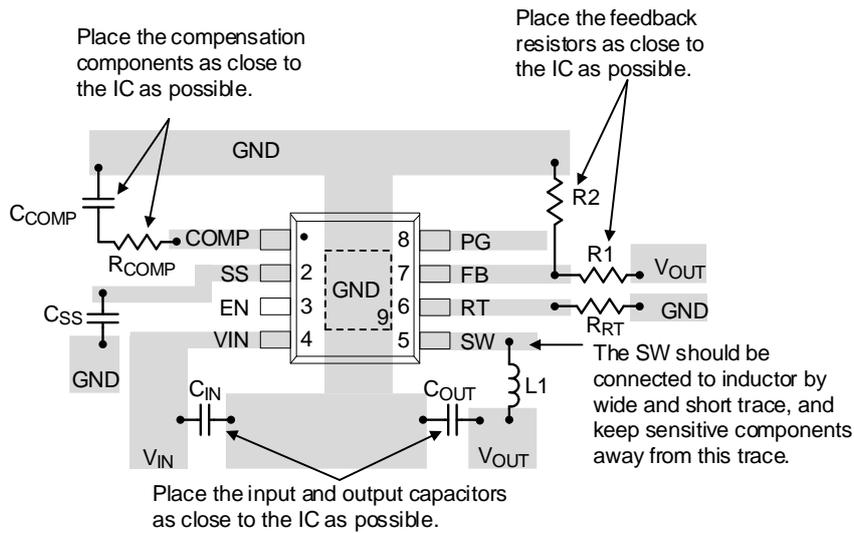


Figure 3. Derating Curves of Maximum Power Dissipation

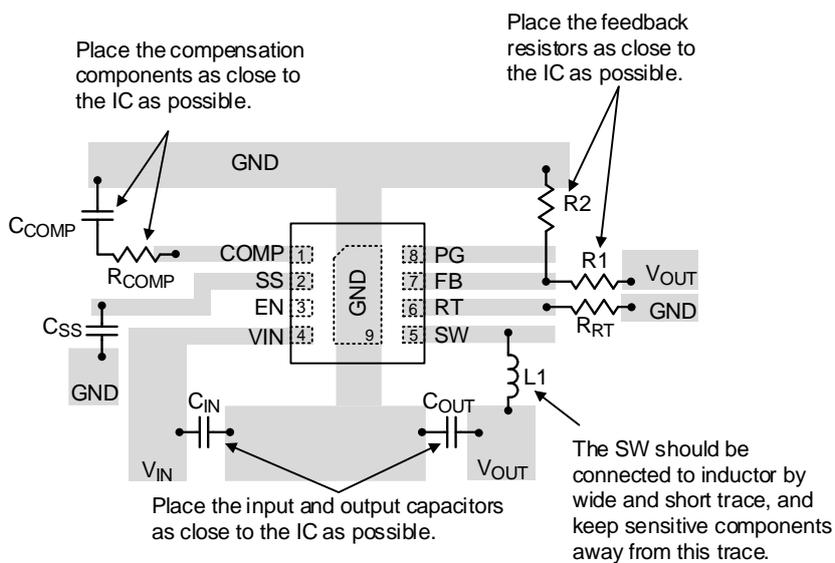
14.13 Layout Considerations

Follow these PCB layout guidelines for optimal performance of the IC.

- Connect the terminal of the input capacitor(s), C_{IN} , as close to the V_{IN} pin as possible. This capacitor provides the AC current into the internal power MOSFETs.
- The SW node experiences high frequency voltage swings, so it should be kept within a small area.
- Keep all sensitive small signal nodes away from the SW node to prevent stray capacitive noise pickup.
- Connect the FB pin directly to the feedback resistors. The resistive voltage divider must be connected between V_{OUT} and GND.



(a) For SOP-8 (Exposed Pad) Package



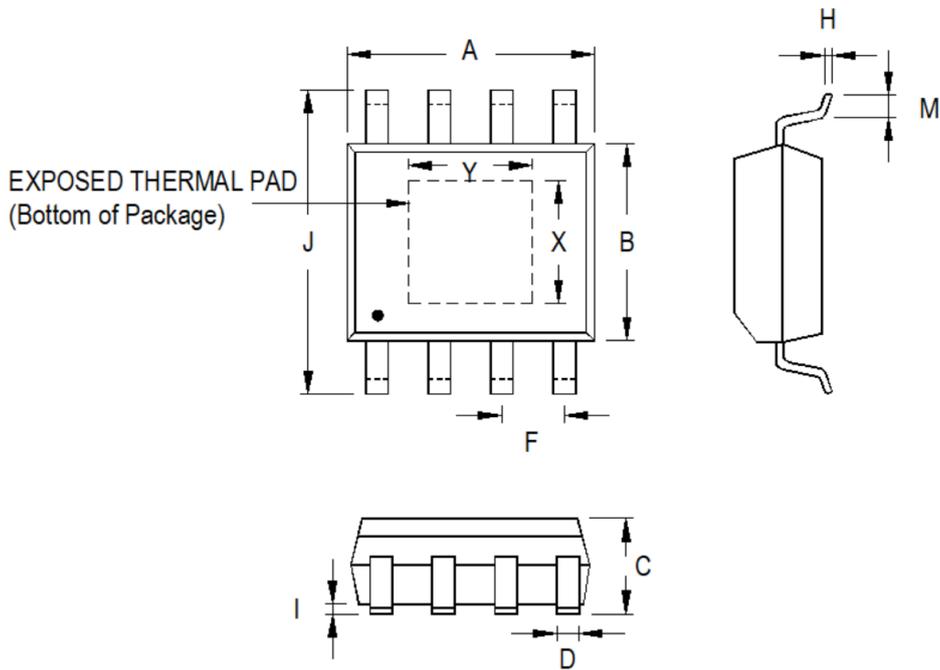
(b) For WDFN-8L 3x3 Package

Figure 4. PCB Layout Guide

Note 7. The information provided in this section is for reference only. The customer is solely responsible for designing, validating, and testing any applications incorporating Richtek’s product(s). The customer is also responsible for applicable standards and any safety, security, or other requirements.

15 Outline Dimension

15.1 SOP-8 (Exposed Pad)

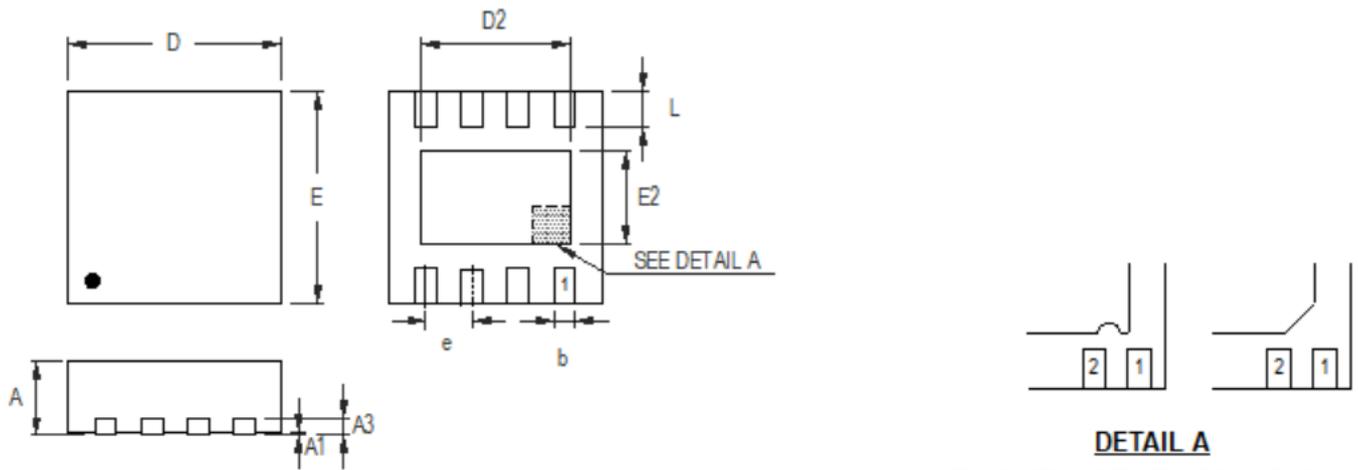


Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	4.801	5.004	0.189	0.197	
B	3.810	4.000	0.150	0.157	
C	1.346	1.753	0.053	0.069	
D	0.330	0.510	0.013	0.020	
F	1.194	1.346	0.047	0.053	
H	0.170	0.254	0.007	0.010	
I	0.000	0.152	0.000	0.006	
J	5.791	6.200	0.228	0.244	
M	0.406	1.270	0.016	0.050	
Option 1	X	2.000	2.300	0.079	0.091
	Y	2.000	2.300	0.079	0.091
Option 2	X	2.100	2.500	0.083	0.098
	Y	3.000	3.500	0.118	0.138

8-Lead SOP (Exposed Pad) Plastic Package

Note 8. The package of the RT8070 uses Option 1.

15.2 WDFN-8L 3x3



DETAIL A
Pin #1 ID and Tie Bar Mark Options

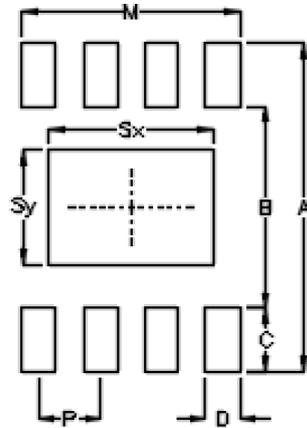
Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.200	0.300	0.008	0.012
D	2.950	3.050	0.116	0.120
D2	2.100	2.350	0.083	0.093
E	2.950	3.050	0.116	0.120
E2	1.350	1.600	0.053	0.063
e	0.650		0.026	
L	0.425	0.525	0.017	0.021

W-Type 8L DFN 3x3 Package

16 Footprint Information

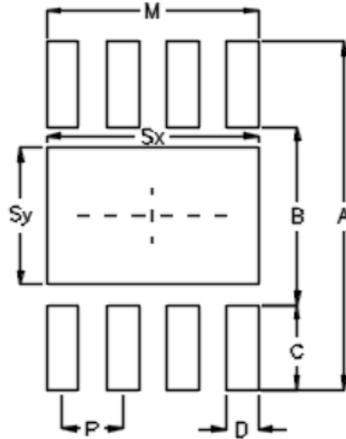
16.1 SOP-8 (Exposed Pad)



Package		Number of Pin	Footprint Dimension (mm)								Tolerance
			P	A	B	C	D	Sx	Sy	M	
PSOP-8	Option1	8	1.27	6.80	4.20	1.30	0.70	2.30	2.30	4.51	±0.10
	Option2							3.40	2.40		

Note 9. The package of the RT8070 uses Option 1.

16.2 WDFN-8L 3x3

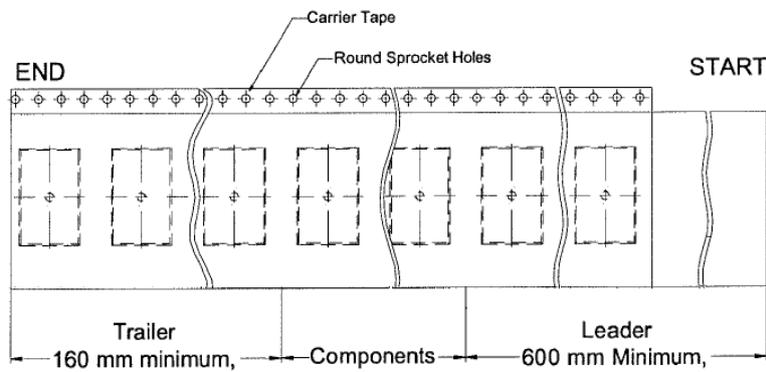
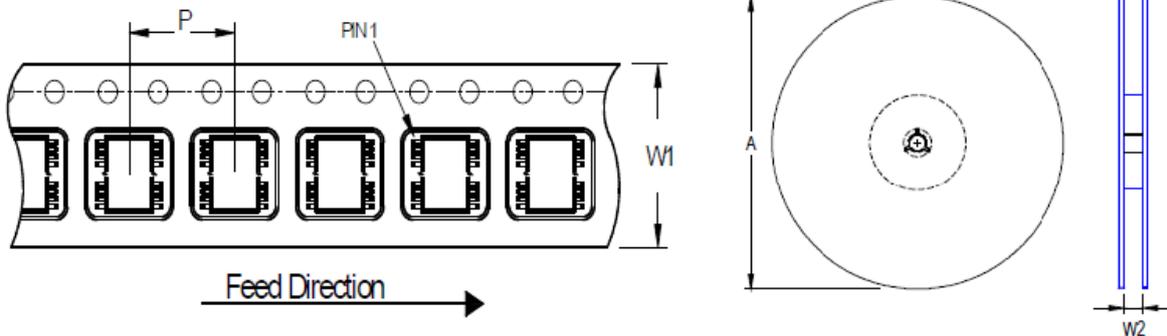


Package	Number of Pin	Footprint Dimension (mm)								Tolerance
		P	A	B	C	D	Sx	Sy	M	
V/W/U/XDFN3*3-8	8	0.65	3.80	1.94	0.93	0.35	2.30	1.50	2.30	±0.05

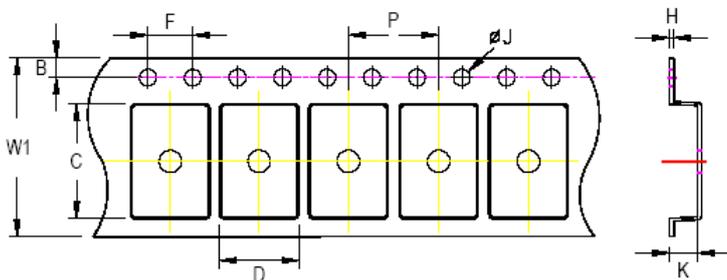
17 Packing Information

17.1 Tape and Reel Data

17.1.1 SOP-8 (Exposed Pad)



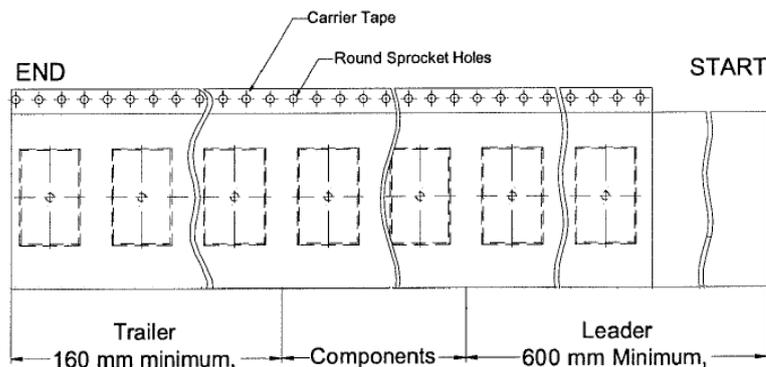
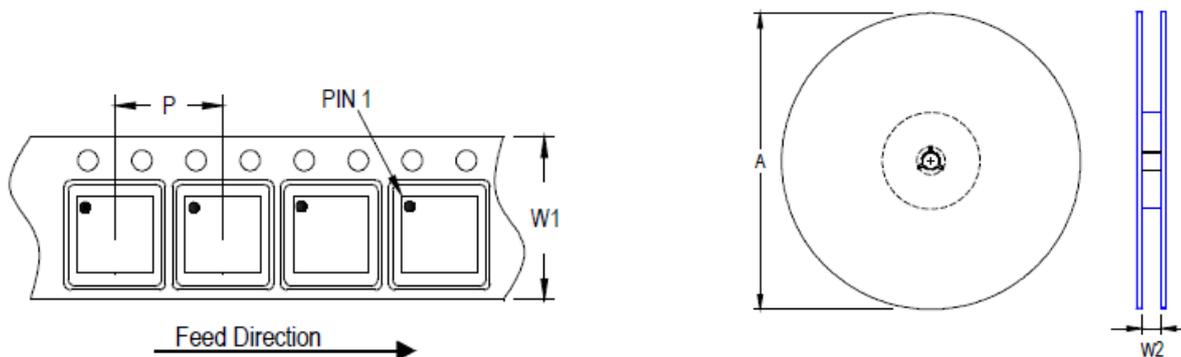
Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
			(mm)	(in)				
PSOP-8	12	8	330	13	2,500	160	600	12.4/14.4



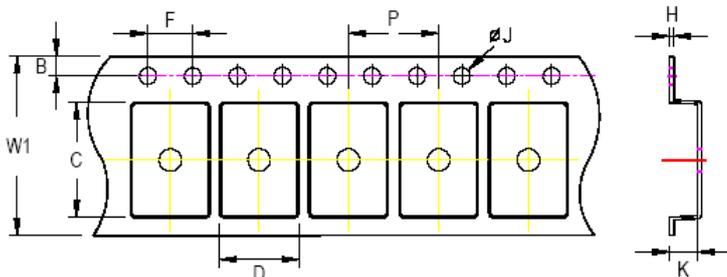
C, D, and K are determined by component size. The clearance between the components and the cavity is as follows:
- For 12mm carrier tape: 0.5mm max.

Tape Size	W1		P		B		F		ØJ		K		H
	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.	
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	1.9mm	2.3mm	0.6mm	

17.1.2 QFN & DFN 3x3



Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
			(mm)	(in)				
(V, W) QFN/DFN 3x3	12	8	180	7	1,500	160	600	12.4/14.4



C, D, and K are determined by component size. The clearance between the components and the cavity is as follows:
 - For 12mm carrier tape: 0.5mm max.

Tape Size	W1		P		B		F		ØJ		K		H
	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.	
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	1.0mm	1.3mm	0.6mm	

17.2 Tape and Reel Packing

17.2.1 SOP-8 (Exposed Pad)

Step	Photo/Description	Step	Photo/Description
1	 Reel 13"	4	 1 reel per inner box Box G
2	 HIC & Desiccant (2 Unit) inside	5	 6 inner boxes per outer box
3	 Caution label is on backside of Al bag	6	 Outer box Carton A

Package \ Container	Reel		Box			Carton		
	Size	Units	Item	Reels	Units	Item	Boxes	Units
PSOP-8	13"	2,500	Box G	1	2,500	Carton A	6	15,000

17.2.2 QFN & DFN 3x3

Step	Photo/Description	Step	Photo/Description
1	 <p>Reel 7"</p>	4	 <p>3 reels per inner box Box A</p>
2	 <p>HIC & Desiccant (1 Unit) inside</p>	5	 <p>12 inner boxes per outer box</p>
3	 <p>Caution label is on backside of Al bag</p>	6	 <p>Outer box Carton A</p>

Package	Reel		Box			Carton		
	Size	Units	Item	Reels	Units	Item	Boxes	Unit
(V, W)	7"	1,500	Box A	3	4,500	Carton A	12	54,000
QFN & DFN 3x3			Box E	1	1,500	For Combined or Partial Reel.		

17.3 Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10^4 to 10^{11}					

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18 Datasheet Revision History

Version	Date	Description	Item
10	2024/10/4	Modify	<i>Changed the name of pin 5 to SW and pin 8 to PG. Ordering Information on page 2 -Added note Electrical Characteristics on page 5 -Modified symbol Footprint Information on page 17, 18 -Added information Packing Information on page 19 to 23 -Added information</i>